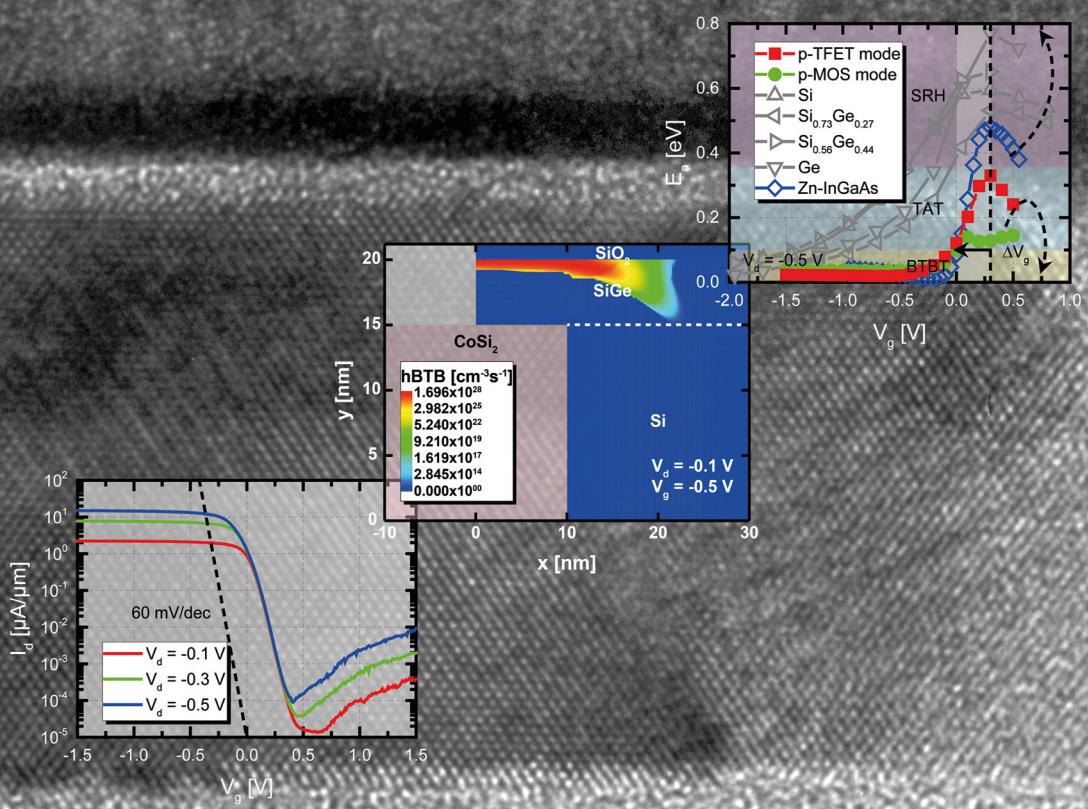


# Strained Silicon-Germanium / Silicon Heterostructure Tunnel FETs for Low Power Applications

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Forschungszentrum Jülich GmbH  
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Semiconductor Nanoelectronics (PGI-9)

# **Strained Silicon-Germanium/Silicon Heterostructure Tunnel FETs for Low Power Applications**

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